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1. Global joint venture starts operations as WeEn Semiconductors

Dear customer.

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

WWW - For www.nxp.com use www.ween-semi.com

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Thank you for your cooperation and understanding,

WeEn Semiconductors



DISCRETE SEMICONDUCTORS

DATA SHEET

BTA216X series B Three quadrant triacs high commutation

Product specification

October 1997



NXP Semiconductors Product specification

Three quadrant triacs high commutation

BTA216X series B

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a full pack, plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

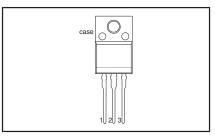
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BTA216X- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500B 500 16 140	600B 600 16 140	800B 800 16 140	V A A

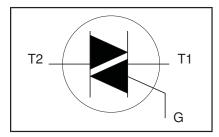
PINNING - SOT186A

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current	full sine wave;	-		16		Α
I _{TSM}	Non-repetitive peak on-state current	$T_{hs} \le 38 ^{\circ}\text{C}$ full sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge					
		t = 20 ms t = 16.7 ms	-		140 150		A A
l ² t dl _T /dt	l ² t for fusing Repetitive rate of rise of on-state current after	t = 10.7 m/s t = 10 m/s $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-		98 100		Α ² s Α/μs
I _{GM} V _{GM} P _{GM} P _{G(AV)}	triggering Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms	- - -		2 5 5 0.5		A V W
${f T}_{stg} \ {f T}_{j}$	Storage temperature Operating junction temperature	period	-40 -		150 125		.C

October 1997 1 Rev 1.200

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	-		2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	full or half cycle with heatsink compound without heatsink compound		-	4.0 5.5	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
			+ G+	2 2	18	50	mA
		T2+	⊦ G-	2	21	50	mA
		T2-	- G-	2	34	50	mA
	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
		T2+	+ G+	-	31	60	mA
		T2+	⊦ G-	-	34	90	mA
		T2-	- G-	-	30	60	mA
l _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		-	31	60	mA
V_{T}	On-state voltage	$I_{T} = 20 \text{ A}$		-	1.2	1.5	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_i = 125 ^{\circ}\text{C}$		0.25	0.4	-	V
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 °C$		-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	4000	-	V/μs
dI _{com} /dt	off-state voltage Critical rate of change of commutating current	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}$; $T_j = 125 ^{\circ}\text{C}$; $I_{T(RMS)} = 16 \text{ A}$; without snubber; gate open circuit	-	28	-	A/ms
t _{gt}	Gate controlled turn-on time	$I_{TM} = 20 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

² Device does not trigger in the T2-, G+ quadrant.

NXP Semiconductors Product specification

Three quadrant triacs high commutation

BTA216X series B

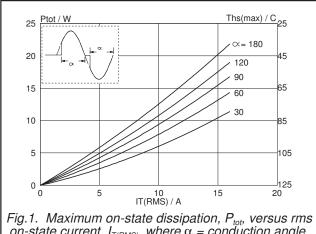


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

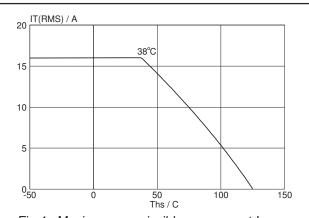


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

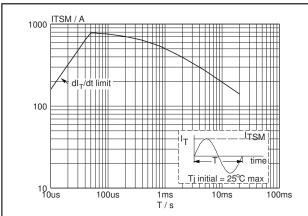


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

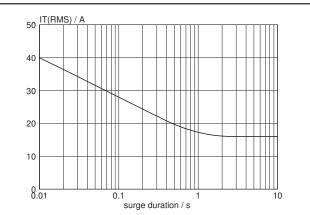


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 38$ °C.

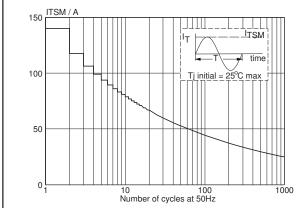


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

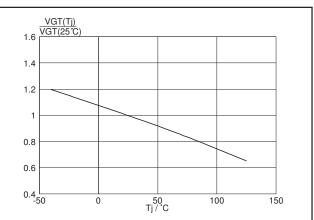
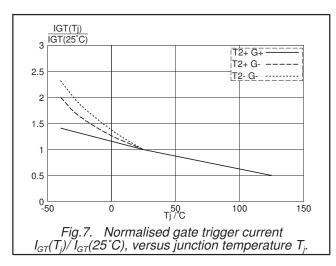


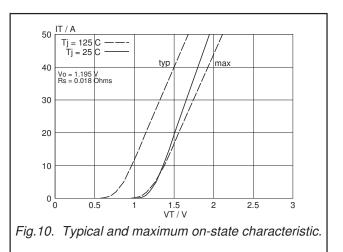
Fig.6. Normalised gate trigger voltage $V_{GT}(T_i)/V_{GT}(25^{\circ}C)$, versus junction temperature T_{i}

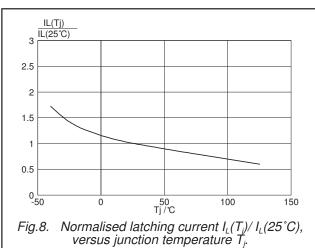
NXP Semiconductors Product specification

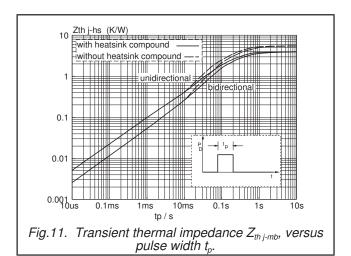
Three quadrant triacs high commutation

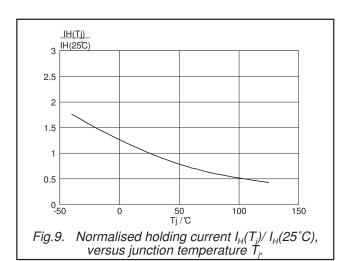
BTA216X series B

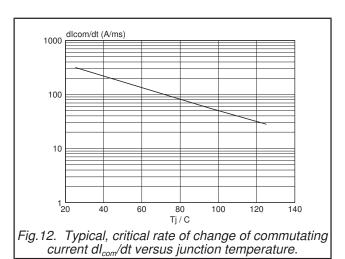










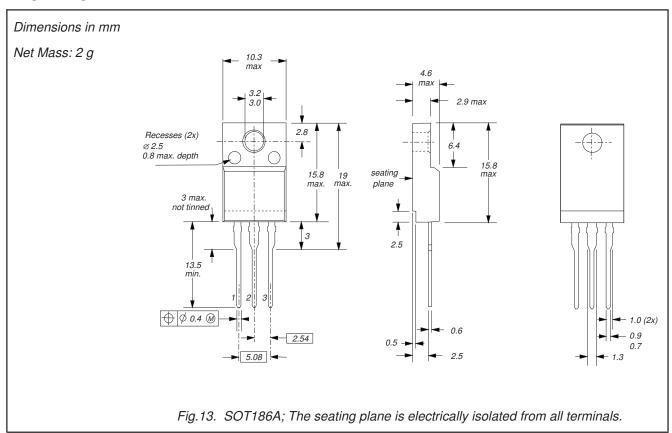


NXP Semiconductors Product specification

Three quadrant triacs high commutation

BTA216X series B

MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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